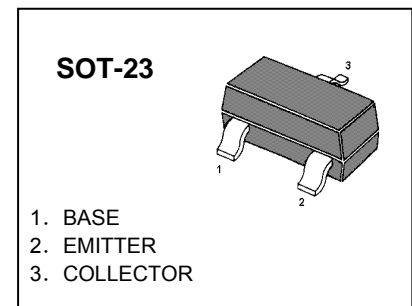


**MMBT2222A TRANSISTOR (NPN)**
**FEATURES**
**Epitaxial planar die construction**
**Complementary PNP Type available(MMBT2907A)**

**MARKING: 1P**
**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Units
<b>V<sub>CB0</sub></b>	Collector-Base Voltage	75	V
<b>V<sub>CEO</sub></b>	Collector-Emitter Voltage	40	V
<b>V<sub>EBO</sub></b>	Emitter-Base Voltage	6	V
<b>I<sub>C</sub></b>	Collector Current -Continuous	600	mA
<b>P<sub>C</sub></b>	Collector Dissipation	300	mW
<b>R<sub>θJA</sub></b>	Thermal Resistance, Junction to Ambient	417	°C/W
<b>T<sub>J</sub></b>	Junction Temperature	150	°C
<b>T<sub>stg</sub></b>	Storage Temperature	-55to+150	°C

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 10μA, I <sub>E</sub> =0	75			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub> *	I <sub>C</sub> = 10mA, I <sub>B</sub> =0	40			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =10μA, I <sub>C</sub> =0	6			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =60V, I <sub>E</sub> =0			0.01	μA
Collector cut-off current	I <sub>CEX</sub>	V <sub>CE</sub> =30V, V <sub>BE(off)</sub> =3V			0.01	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 3V, I <sub>C</sub> =0			0.1	μA
DC current gain	h <sub>FE(1)</sub> *	V <sub>CE</sub> =10V, I <sub>C</sub> = 150mA	100		300	
	h <sub>FE(2)</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> = 0.1mA	40			
	h <sub>FE(3)</sub> *	V <sub>CE</sub> =10V, I <sub>C</sub> = 500mA	42			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub> *	I <sub>C</sub> =500 mA, I <sub>B</sub> = 50mA I <sub>C</sub> =150 mA, I <sub>B</sub> =15mA			1 0.3	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub> *	I <sub>C</sub> =500 mA, I <sub>B</sub> = 50mA I <sub>C</sub> =150 mA, I <sub>B</sub> =15mA			2.0 1.2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =20V, I <sub>C</sub> = 20mA, f=100MHz	300			MHz
Delay time	t <sub>d</sub>	V <sub>CC</sub> =30V, V <sub>BE(off)</sub> =-0.5V I <sub>C</sub> =150mA, I <sub>B1</sub> = 15mA			10	nS
Rise time	t <sub>r</sub>				25	nS
Storage time	t <sub>s</sub>	V <sub>CC</sub> =30V, I <sub>C</sub> =150mA I <sub>B1</sub> =-I <sub>B2</sub> =15mA			225	nS
Fall time	t <sub>f</sub>				60	nS

\*pulse test: Pulse Width ≤300μs, Duty Cycles ≤ 2.0%.

Typical Characteristics

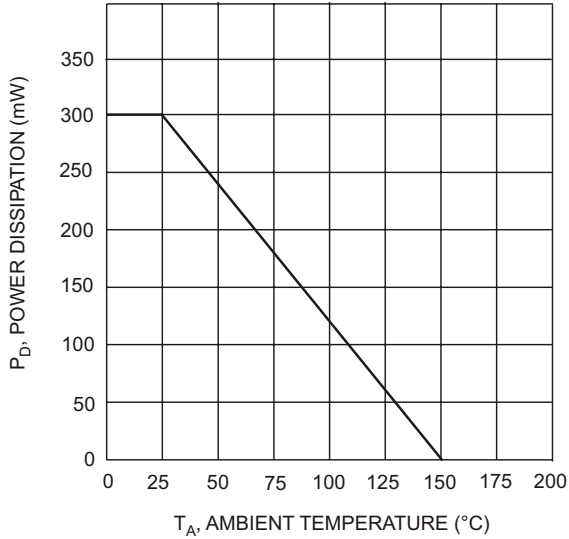


Fig. 1, Max Power Dissipation vs Ambient Temperature

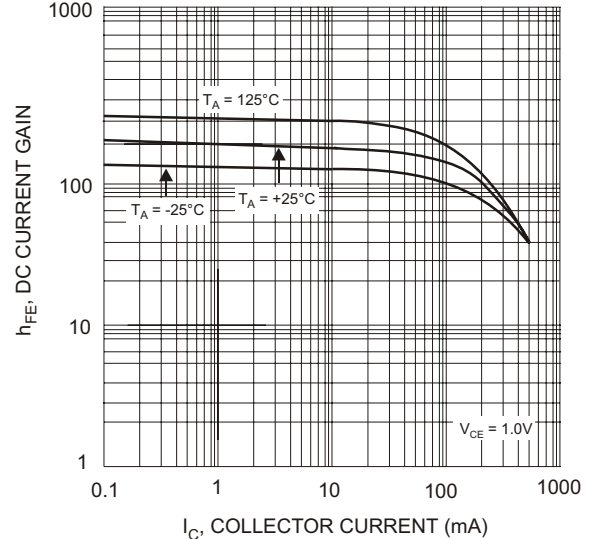


Fig. 2, Typical DC Current Gain vs Collector Current

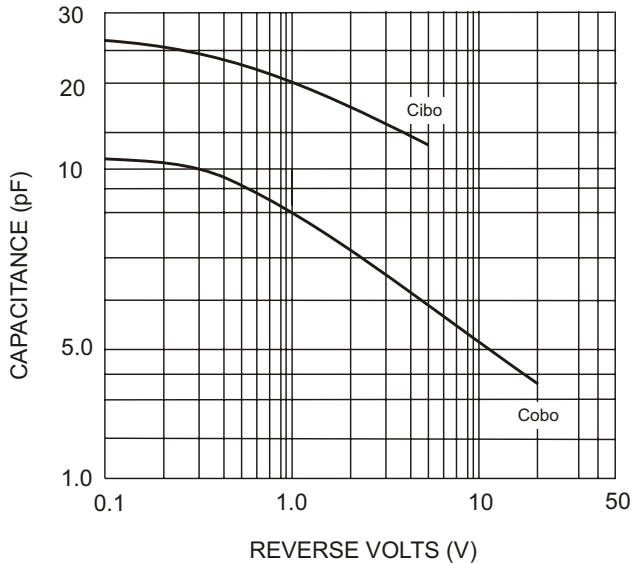


Fig. 3 Typical Capacitance

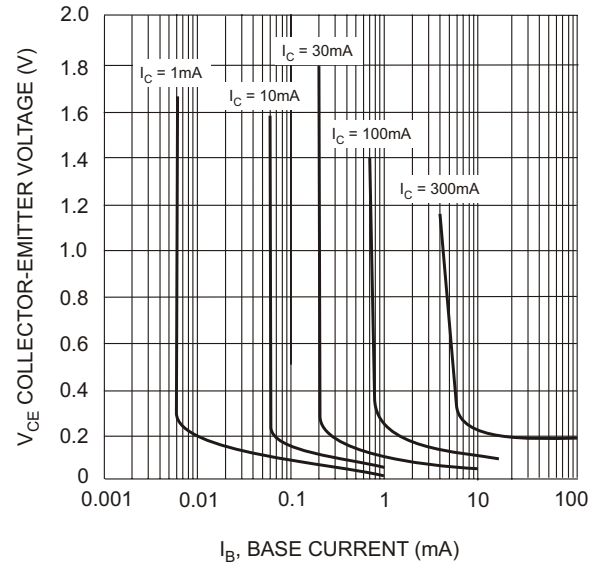
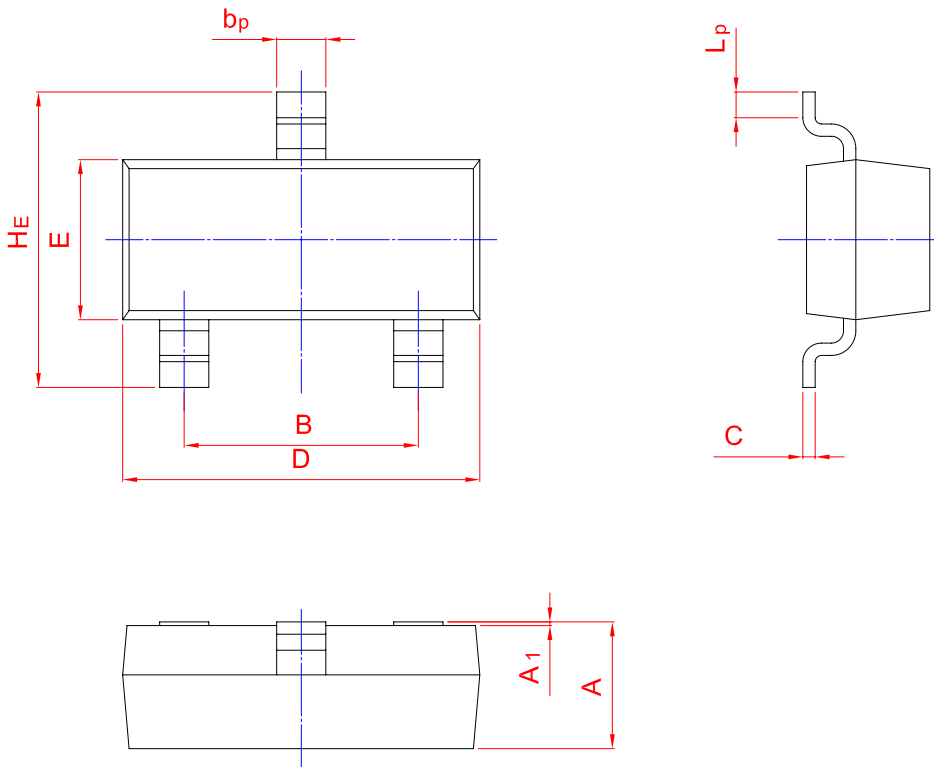


Fig. 4 Typical Collector Saturation Region

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	$b_p$	C	D	E	$H_E$	$A_1$	$L_p$
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20

单击下面可查看定价，库存，交付和生命周期等信息

[>>TWGMC\(台湾迪嘉\)](#)